

# **JHH40N120FA2**

# **Product Preview**

1200V/40A FIELD-STOP TRENCH IGBT WITH DIODE



#### **Features**

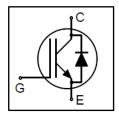
- Low V<sub>CE(sat)</sub>
- Fast Switching
- High Ruggedness
- Short-Circuit Rated



Product Summary					
V <sub>CES</sub> 1200V					
I <sub>C</sub>	40A <sup>(1)</sup>				
$V_{CE(sat),typ}$	1.75V (T <sub>J</sub> = 25°C)				
Package	TO-247				

### **Applications**

- Inverters
- Frequency Converters
- Industrial Motor Drives
- Uninterrupted Power Supply





#### **Ordering Information**

Part Number	Marking	Package	Packaging
JHH40N120FA2	HH40N120FA2	TO-247	Tube

### **Absolute Maximum Ratings**

Parameter	Symbol	Limit	Unit
Collector-to-Emitter Voltage	V <sub>CES</sub>	1200	V
Gate-to-Emitter Voltage	$V_{GES}$	±20	v
DC Collector Current (T <sub>c</sub> = 25°C, T <sub>J</sub> = 175°C)		61	
DC Collector Current (T <sub>c</sub> = 100°C, T <sub>J</sub> = 175°C)	l <sub>c</sub>	40	
Pulsed Collector Current (pulse width limited by maximum $T_j$ )	I <sub>CM</sub>	160	]
Diode Forward Current (T <sub>c</sub> = 25°C, T <sub>J</sub> = 175°C)		67	Α
Diode Forward Current (T <sub>c</sub> = 100°C, T <sub>J</sub> = 175°C)	- I <sub>F</sub>	43	
Diode Pulsed Current (pulse width limited by maximum T <sub>J</sub> )	I <sub>FM</sub>	160	
Short Circuit Withstand Time ( $V_{GE} = 15V$ , $V_{CC} \le 600V$ , $T_{J\_start} \le 175$ °C)	t <sub>SC</sub>	10	μs
Turn-off Safe Operating Area (V <sub>CE</sub> ≤ 1200V, T <sub>J</sub> ≤ 175°C)	-	160	Α
Maximum Power Dissipation (T <sub>c</sub> = 25°C, T <sub>J</sub> = 175°C)	P <sub>D(max)</sub>	258	W
Operating Junction Temperature	T <sub>J</sub>	-40 to +175	
Storage Temperature	T <sub>stg</sub>	-55 to +150	°C
Maximum Lead Temperature for Soldering (1/8" from case for 5 seconds)	T <sub>sld</sub>	260	



# Static Electrical Characteristics (2)

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Collector-to-Emitter Breakdown Voltage	BV <sub>CES</sub>	V <sub>GE</sub> = 0V, I <sub>C</sub> = 250μA	1200	-	-	V
		V <sub>CE</sub> = 1200V, V <sub>GE</sub> = 0V	-	-	10	μΑ
Collector-to-Emitter Leakage Current	I <sub>CES</sub>	$V_{CE} = 1200V, V_{GE} = 0V,$ $T_{J} = 150^{\circ}C$	-	-	5	mA
		$V_{CE} = 1200V, V_{GE} = 0V,$ $T_{J} = 175^{\circ}C$	-	-	20	mA
Gate-to-Emitter Leakage Current	I <sub>GES</sub>	$V_{CE} = 0V, V_{GE} = \pm 20V$	-	-	100	nA
Gate Threshold Voltage	V <sub>GE(th)</sub>	$V_{CE} = V_{GE}$ , $I_C = 1.5$ mA	5.5	6.5	7.5	
		V <sub>GE</sub> = 15V, I <sub>C</sub> = 40A	-	1.75	2.1	
Collector-to-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	$V_{GE} = 15V, I_{C} = 40A,$ $T_{J} = 150^{\circ}C$	-	2.3	-	
		$V_{GE} = 15V, I_{C} = 40A,$ $T_{J} = 175^{\circ}C$	-	2.45	-	V
		V <sub>GE</sub> = 0V, I <sub>F</sub> = 40A	-	2.15	2.6	
Diode Forward Voltage	V <sub>F</sub>	$V_{GE} = 0V, I_F = 40A$ $T_J = 150^{\circ}C$	-	2.35	-	
		V <sub>GE</sub> = 0V, I <sub>F</sub> = 40A T <sub>J</sub> =175°C	-	2.25	-	

#### **Thermal Characteristics**

Parameter	Symbol	Min	Тур	Max	Unit
Junction-to-Ambient Thermal Resistance	$R_{\theta JA}$	-	-	40	
Junction-to-Case Thermal Resistance, IGBT	D	-	-	0.58	°C/W
Junction-to-Case Thermal Resistance, Diode	R <sub>θJC</sub>	-	-	0.6	

# **Dynamic Electrical Characteristics** (2)

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Total Gate Charge	$Q_{\mathrm{g}}$	$V_{CC} = 600V$ , $V_{GE} = 15V$ , $I_C = 40A$	-	148	ı	nC
Input Capacitance	C <sub>iss</sub>	V <sub>CE</sub> = 25V,	-	3460	-	
Output Capacitance	C <sub>oss</sub>	$V_{GE} = 0V$ ,	-	154	-	pF
Reverse Transfer Capacitance	C <sub>rss</sub>	f = 1MHz	-	41	-	



## Switching Characteristics, Inductive Load (2), (3)

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Turn-on Delay time	t <sub>d(ON)</sub>	V 600V	-	45	-	
Rise Time	t <sub>r</sub>	$V_{CC} = 600V,$ $V_{GE} = 0/15V,$	-	58	-	
Turn-off Delay time	t <sub>d(OFF)</sub>	$R_G = 10\Omega$ , $I_C = 40A$ ,	-	165	-	ns
Fall Time	t <sub>f</sub>	$L_{load} = 0.82 \text{mH},$	-	110	-	
Turn-On Switching Loss	E <sub>on</sub>	Energy losses include "tail" and diode	-	2.9	-	
Turn-Off Switching Loss	E <sub>off</sub>	reverse recovery.	-	1.8	-	mJ
IGBT Total Switching Loss	E <sub>ts</sub>		-	4.7	-	
Diode Reverse-Recovery Time	t <sub>rr</sub>	V <sub>R</sub> = 600V,	-	195	-	ns
Diode Reverse-Recovery Charge	Q <sub>rr</sub>	I <sub>F</sub> = 40A,	-	1500	-	nC
Diode Peak Reverse-Recovery Current	I <sub>rrm</sub>	dl <sub>F</sub> /dt = 672A/μs	-	18	-	Α
Short Circuit Collector Current (T <sub>J</sub> = 25°C)	I <sub>C(SC)</sub>	$V_{GE} = 15V,$ $V_{CC} \le 600V,$ $t_{SC} \le 10\mu s$	-	160	-	А

<sup>(1)</sup> DC collector current,  $T_c = 100$ °C,  $T_J = 175$ °C.

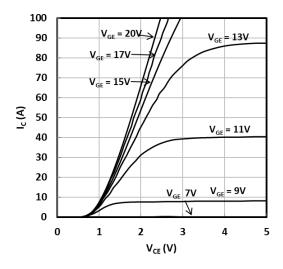
 $E_{on}\!\!:$  from 10% of  $V_{GE}$  to 10% of  $V_{CE};\quad E_{off}\!\!:$  from 90% of  $V_{GE}$  to 10% of Ic.

<sup>(2)</sup>  $T_J = 25$ °C unless otherwise specified

<sup>(3)</sup>  $t_r$ : from 10% of Ic to 90% of Ic;  $t_f$ : from 90% of Ic to 10% of Ic;



#### **Typical Electrical Characteristics**



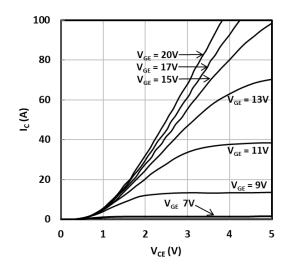


Fig. 1 Typical output characteristics

$$(T_J = 25 \, ^{\circ}\text{C}, t_p = 250 \, \mu\text{s})$$

80 70

60

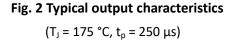
50

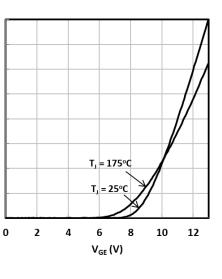
20

10

0

€ 40 30





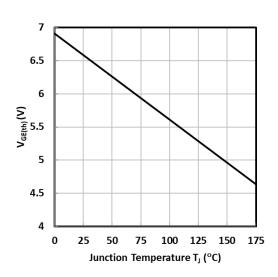


Fig. 3 Typical transfer characteristics

$$(V_{CE} = 20 \text{ V}, t_p = 250 \mu\text{s})$$

Fig. 4 Typical gate threshold voltage as a function of junction temperature

$$(V_{CE} = V_{GE}, I_C = 1.5mA)$$



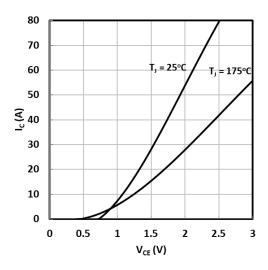


Fig. 5 Typical saturation voltage characteristics

(V<sub>GE</sub> = 15 V, 
$$t_p$$
 = 250  $\mu$ s)

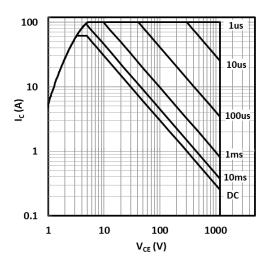


Fig. 7 Safe operating area

(D = 0, 
$$T_{C}$$
 = 25 °C,  $V_{GE}$  = 15 V,  $T_{J} \leq$  175 °C)

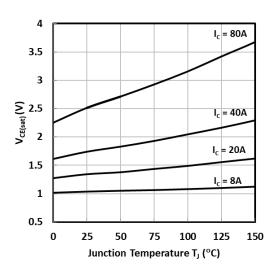


Fig. 6 Typical saturation voltage as a function of junction temperature

$$(V_{GE} = 15 \text{ V}, t_p = 250 \mu\text{s})$$

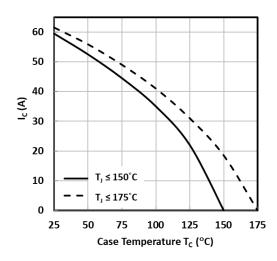


Fig. 8 Maximum DC collector current as a function of case temperature



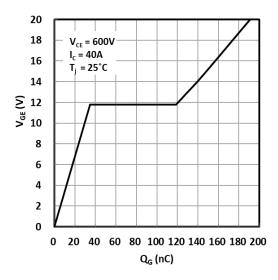
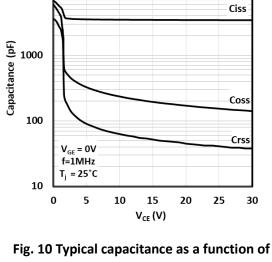


Fig. 9 Typical gate charge characteristics



10000

Fig. 10 Typical capacitance as a function of collector-to-emitter voltage

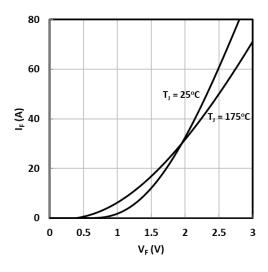


Fig. 11 Typical diode forward current as a function of forward voltage

$$(V_{GE} = 0 V, t_p = 250 \mu s)$$

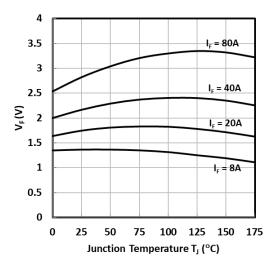
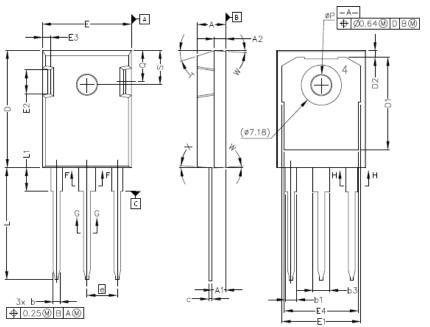
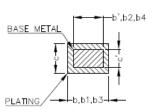


Fig. 12 Typical diode forward voltage as a function of junction temperature



## **Package Drawing**





0.01	MILLIM	ETERS	INC	HES
SYM	MIN	MAX	MIN	MAX
A	4.83	5.21	.190	.205
A1	2.29	2.54	.090	.100
A2	1.91	2.16	.075	.085
b'	1.07	1.28	.042	.050
ь	1.07	1.33	.042	.052
b1	1.91	2.41	.075	.095
b2	1.91	2.16	.075	.085
b3	2.87	3.38	.113	.133
b4	2.87	3.13	.113	.123
c'	0.55	0.65	.022	.026
С	0.55	0.68	.022	.027
D	20.80	21.10	.819	.831
D1	16.25	17.65	.640	.695
D2	0.95	1.25	.037	.049
E	15.75	16.13	.620	.635
E1	13.10	14.15	.516	.557
E2	3.68	5.10	.145	.201
E3	1.00	1.90	.039	.075
E4	12.38	13.43	.487	.529
e	5.44 BSC		.214 E	BSC
N	3			3
L	19.81	20.32	.780	.800
L1	4.10	4.40	.161	.173
φP	3.51	3.65	.138	.144
Q	5.49	6.00	.216	.236
S	6.04	6.30	.238	.248
T		17.5° R		
W		3.5° RE	EF.	
X		4° REF	1_	

TO-247





#### Revision history of JHH40N120FA2 Specification

Version	Change Items	Effective Date	
1.00	Initial Release	17-Jun-20	



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